PNP Silicon High Voltage Transistor

Features

- Halogen Free. “Green” Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

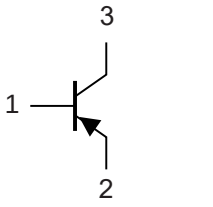
- Operating Junction Temperature Range: -55℃ to +150℃
- Storage Temperature Range: -55℃ to +150℃
- Thermal Resistance: 556℃/W Junction to Ambient(Note 2)
- Thermal Resistance: 417℃/W Junction to Ambient(Note 3)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-300	mA
Peak Collector Current	I_{CM}	-500	mA
Power Dissipation(Note 2)	P_D	225	mW
Power Dissipation(Note 3)	P_D	300	mW

Note:
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. Device Mounted on FR–5 Board.
3. Device with Alumina Substrate.

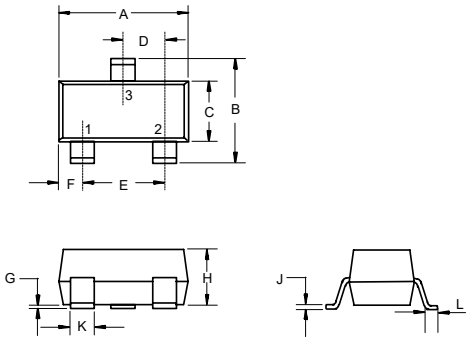
Marking: 2D

Internal Structure



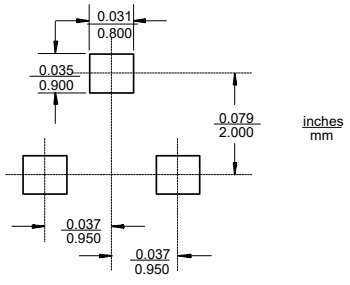
1.BASE
2.EMITTER
3.COLLECTOR

SOT-23



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ T_A=25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300			V	I_C=-1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_C=0
Collector Cutoff Current	I_{CBO}			-0.25	μA	V_{CB}=-200V, I_E=0
Emitter Cutoff Current	I_{EBO}			-0.1	μA	V_{EB}=-5V, I_C=0
DC Current Gain	$h_{FE(1)}$	60				V_{CE}=-10V, I_C=-1mA
	$h_{FE(2)}$	100		200		V_{CE}=-10V, I_C=-10mA
	$h_{FE(3)}$	60				V_{CE}=-10V, I_C=-30mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.2	V	I_C=-20mA, I_B=-2mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.9	V	I_C=-20mA, I_B=-2mA
Transition Frequency	f_T	50			MHz	V_{CE}=-20V, I_C=-10mA, f=30MHz
Collector output Capacitance	C_{cb}			6	pF	V_{CB}=-20V, I_E=0,f=1MHz

Curve Characteristics

Fig. 1 - Static Characteristics

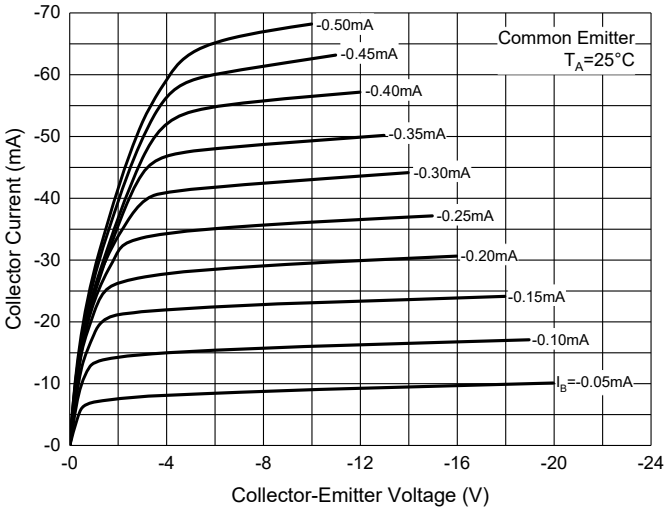


Fig. 2 - DC Current Gain Characteristics

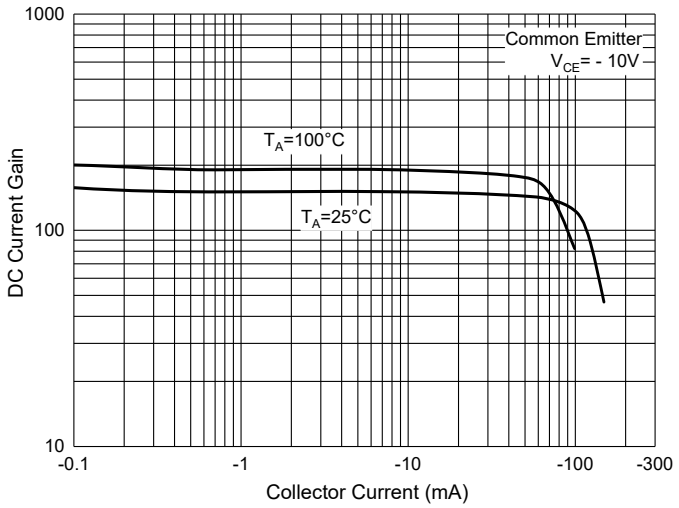


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

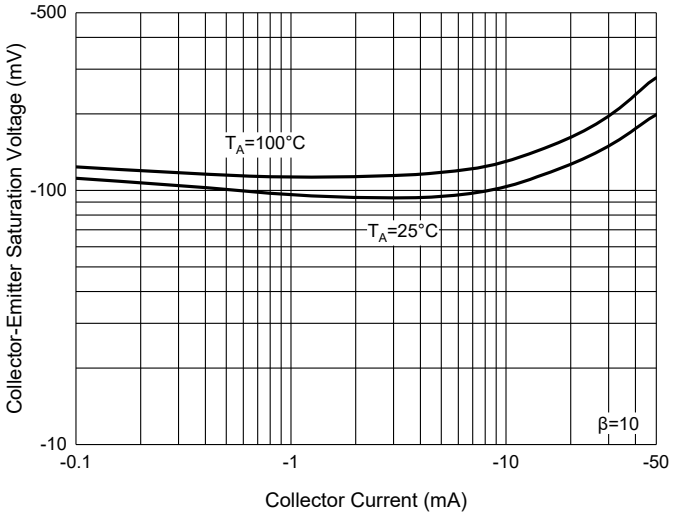


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

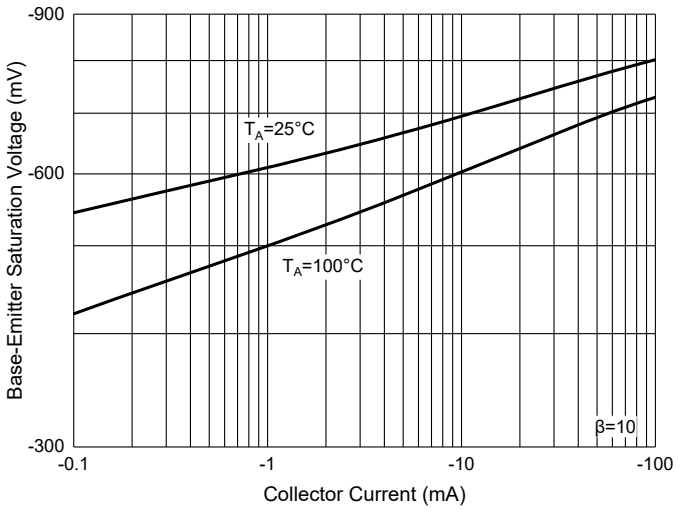


Fig. 5 - Base-Emitter Voltage Characteristics

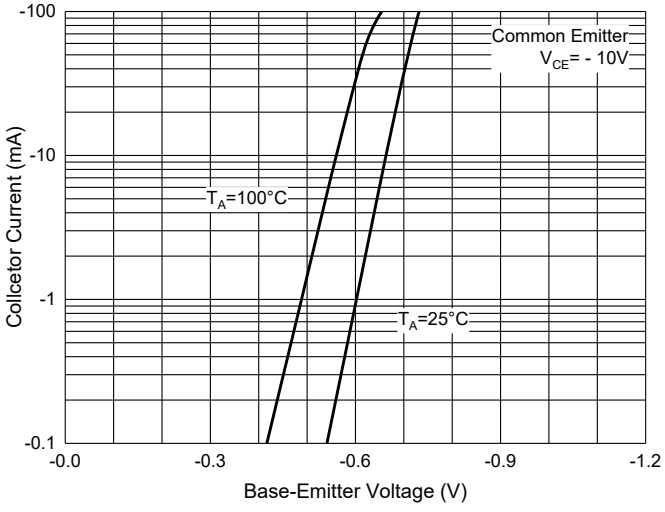


Fig. 6 - Collector Power Derating Curve